

**Features**

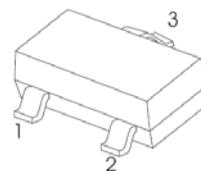
- $V_{DS}$  (V) = 20V
- $R_{DS(ON)} < 46m\Omega$  ( $V_{GS} = 4.5V$ )
- $R_{DS(ON)} < 66m\Omega$  ( $V_{GS} = 2.5V$ )

**Application(s)**

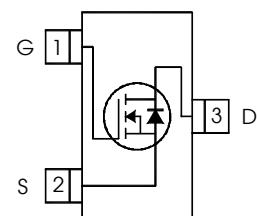
- Load/ System Switch

**Benefits**

- Multi-vendor compatibility
- Environmentally friendly
- Increased Reliability

**SOT - 23**

1. GATE
2. SOURCE
3. DRAIN

**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	20	V
$I_D$ @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.1	A
$I_D$ @ $T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	3.3	
$I_{DM}$	Pulsed Drain Current	16	
$P_D$ @ $T_A = 25^\circ C$	Maximum Power Dissipation	1.3	W
$P_D$ @ $T_A = 70^\circ C$	Maximum Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/ $^\circ C$
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	100	100	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient ( $t < 10s$ ) ④		99	

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ Surface mounted on 1 in square Cu board

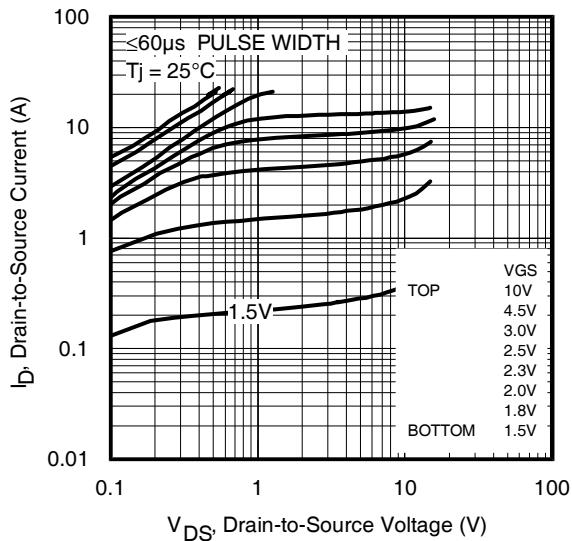
**Electric Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	20		V		$V = 0V, I = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient		0.03		V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I = 1\text{mA}$
$R_{\text{DS}(\text{on})}$	Static Drain-to-Source On-Resistance	30	46		$\text{m}\Omega$	$V = 4.5V, I = 4.1\text{A}$ ②
		45	66			$V = 2.5V, I = 3.3\text{A}$ ②
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	0.5	0.8	1.1	V	$V = V_g, I = 5\mu\text{A}$
$I_{\text{DSS}}$	Drain-to-Source Leakage Current		1.0		$\mu\text{A}$	$V = 16V, V_g = 0V$
			10			$V = 16V, V_g = 0V, T = 55^\circ\text{C}$
			150			$V = 16V, V_g = 0V, T = 125^\circ\text{C}$
$I_{\text{GSS}}$	Gate-to-Source Forward Leakage		100		$\text{nA}$	$V = 12V$
	Gate-to-Source Reverse Leakage		-100			$V = -12V$
$R_G$	Internal Gate Resistance		4.0		$\Omega$	
$g_{\text{fs}}$	Forward Transconductance	10			S	$V = 10V, I = 4.1\text{A}$
$Q_g$	Total Gate Charge		3.5		nC	$I = 4.1\text{A}$
$Q_{\text{gs}}$	Gate-to-Source Charge		0.26			$V = 10V$
$Q_{\text{gd}}$	Gate-to-Drain ("Miller") Charge		1.7			$V = 4.5V$ ②
$t_{\text{d}(\text{on})}$	Turn-On Delay Time		3.6		ns	$V = 10V$ ②
$t_r$	Rise Time		4.9			$I = 1.0\text{A}$
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time		11			$R = 6.8\Omega$
$t_f$	Fall Time		6.0			$V = 4.5V$
$C_{\text{iss}}$	Input Capacitance		290		pF	$V = 0V$
$C_{\text{oss}}$	Output Capacitance		64			$V = 16V$
$C_{\text{rss}}$	Reverse Transfer Capacitance		41			$f = 1.0\text{MHz}$

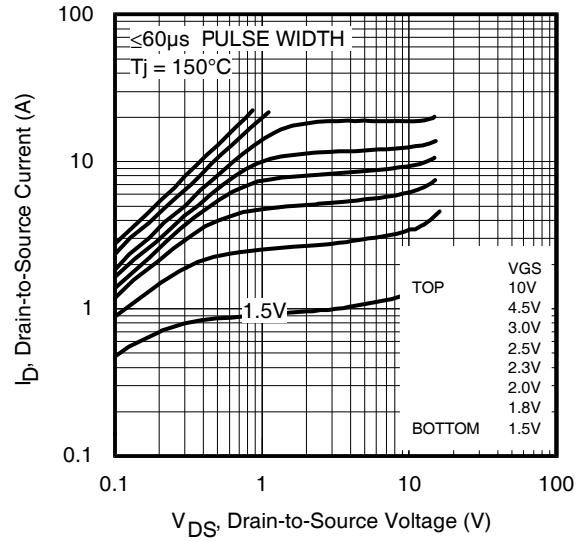
**Source - Drain Ratings and Characteristics**

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_s$	Continuous Source Current (Body Diode)			1.3	A	MOSFET symbol
	Pulsed Source Current (Body Diode) ①			16		integral reverse
$V_{\text{SD}}$	Diode Forward Voltage			1.2	V	$T = 25^\circ\text{C}, I = 4.1\text{A}, V_g = 0V$ ②
$t_{\text{rr}}$	Reverse Recovery Time		8.6	13	ns	$T = 25^\circ\text{C}, V_g = 15V, I = 1.3\text{A}$
$Q_{\text{rr}}$	Reverse Recovery Charge		2.8	4.2		$dI/dt = 100\text{A}/\mu\text{s}$ ②

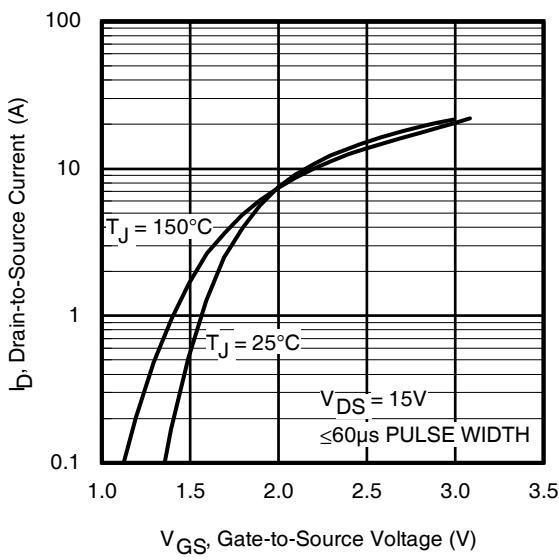
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



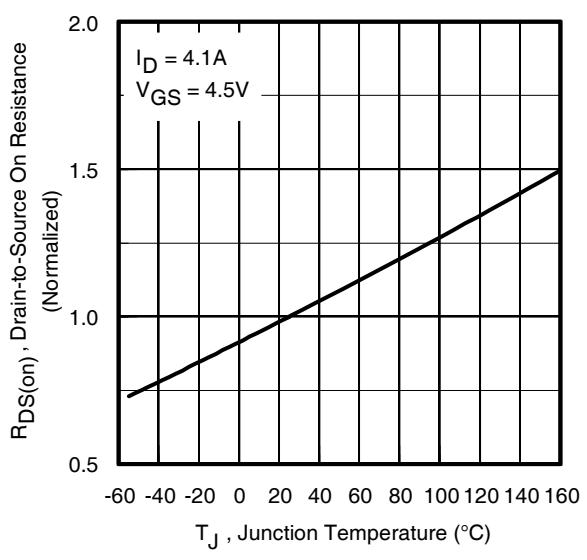
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

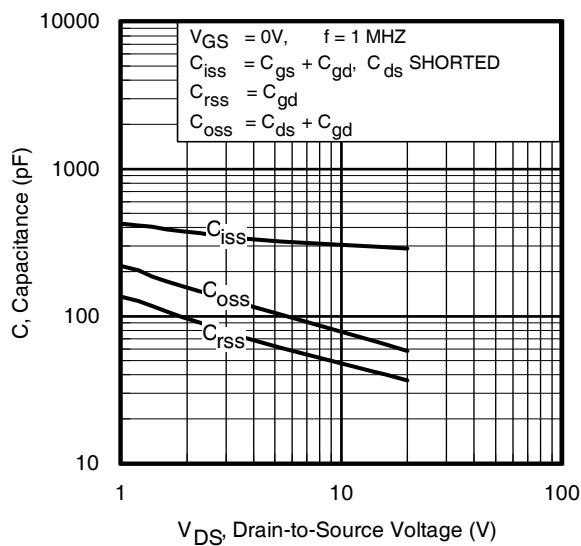


**Fig 3.** Typical Transfer Characteristics

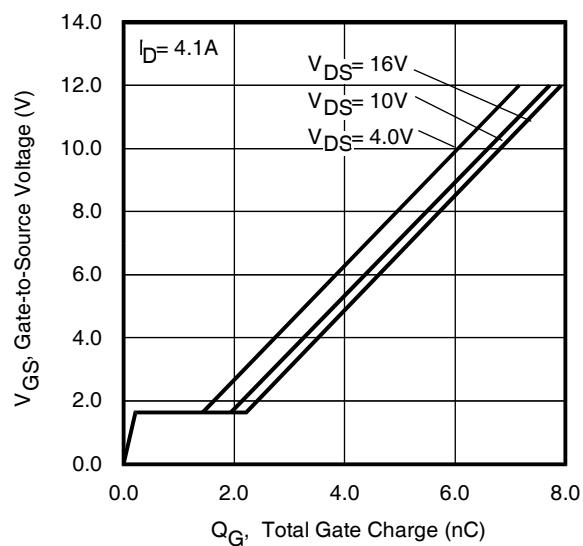


**Fig 4.** Normalized On-Resistance Vs. Temperature

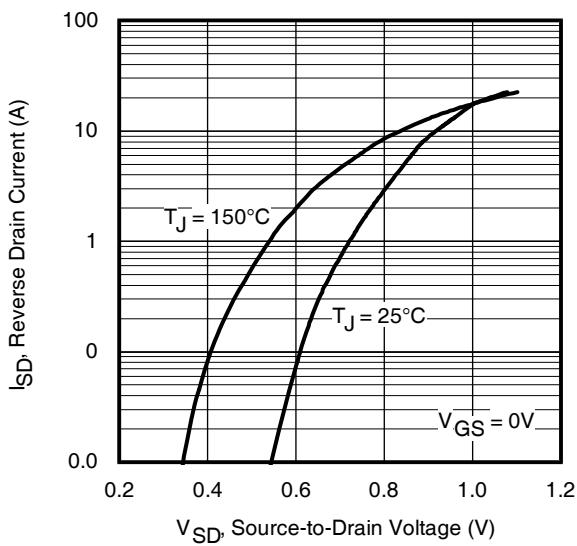
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



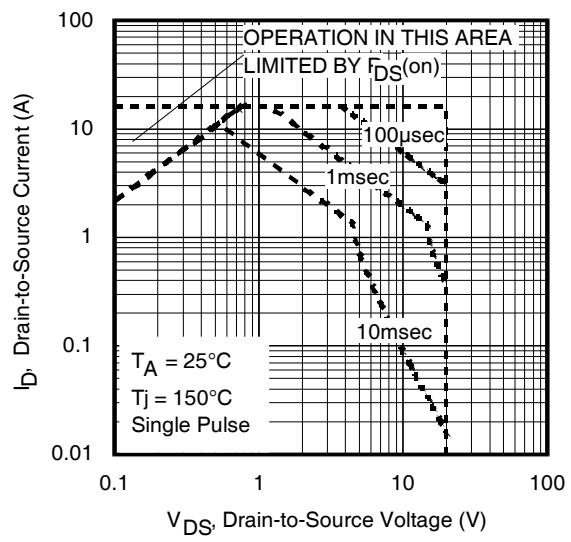
**Fig 5.** Typical Capacitance Vs.  
Drain-to-Source Voltage



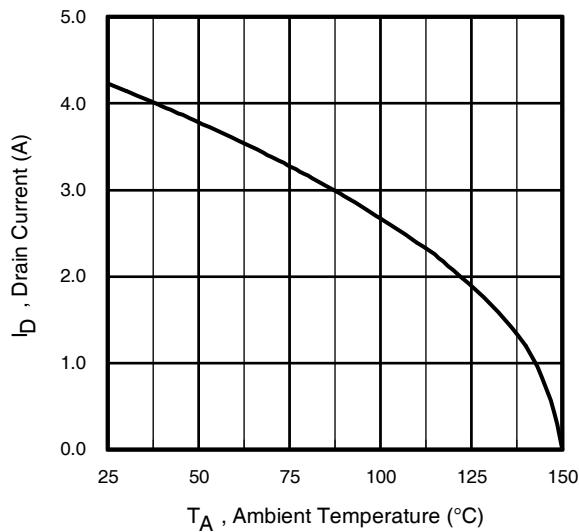
**Fig 6.** Typical Gate Charge Vs.  
Gate-to-Source Voltage



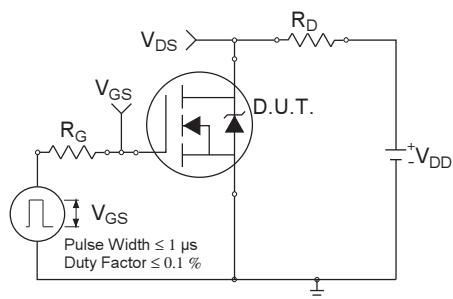
**Fig 7.** Typical Source-Drain Diode  
Forward Voltage



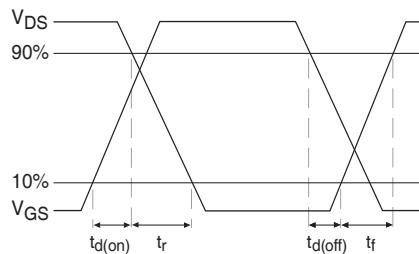
**Fig 8.** Maximum Safe Operating Area



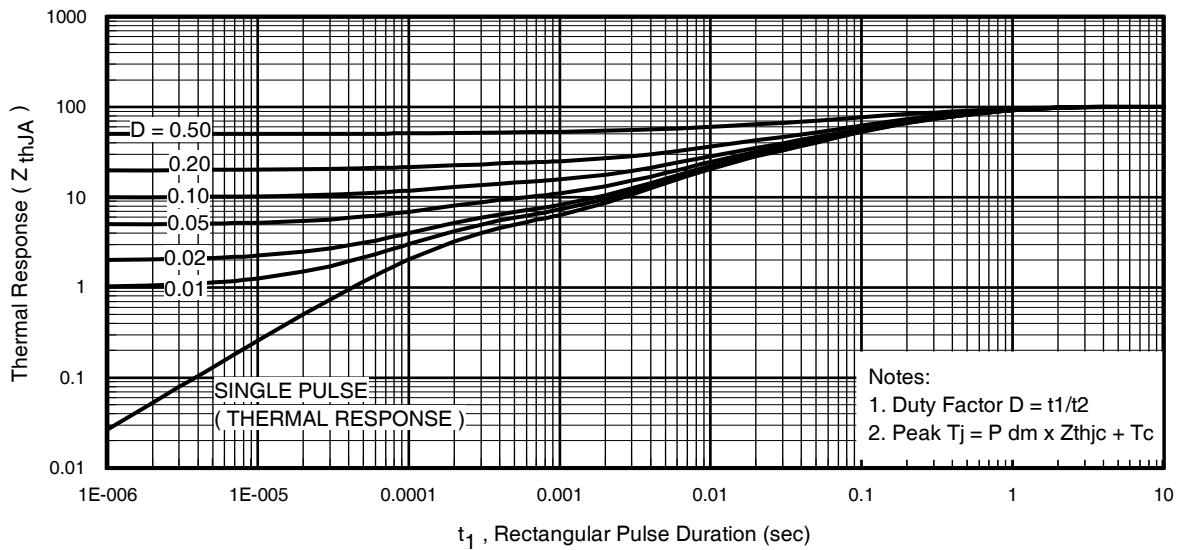
**Fig 9.** Maximum Drain Current Vs.  
Ambient Temperature



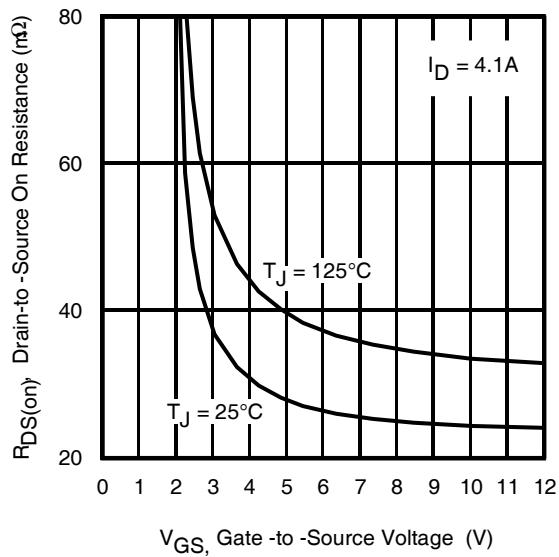
**Fig 10a.** Switching Time Test Circuit



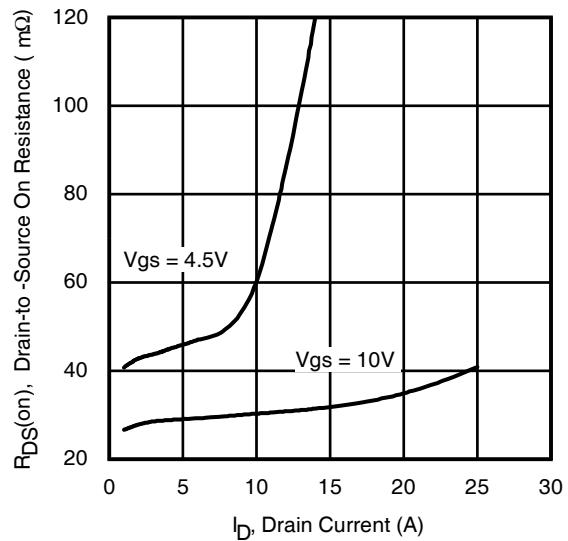
**Fig 10b.** Switching Time Waveforms



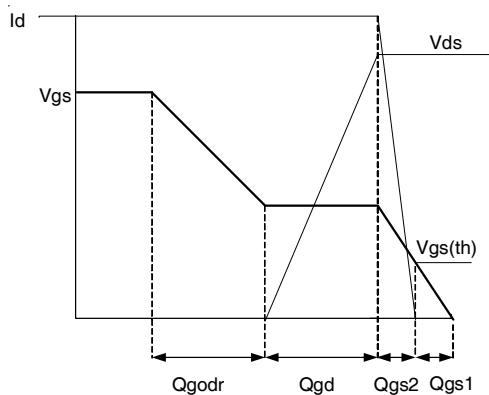
**Fig 11.** Typical Effective Transient Thermal Impedance, Junction-to-Ambient



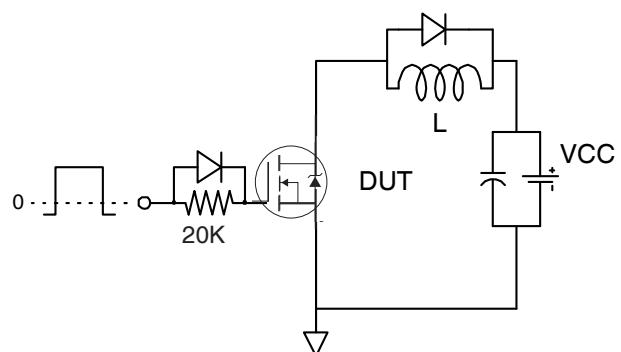
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



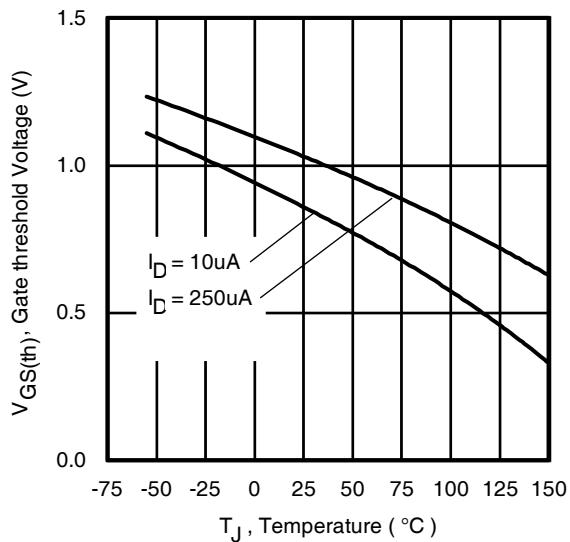
**Fig 13.** Typical On-Resistance Vs. Drain Current



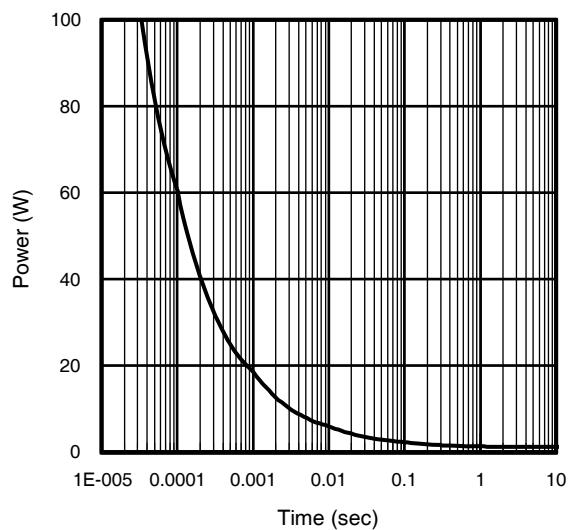
**Fig 14a.** Basic Gate Charge Waveform



**Fig 14b.** Gate Charge Test Circuit

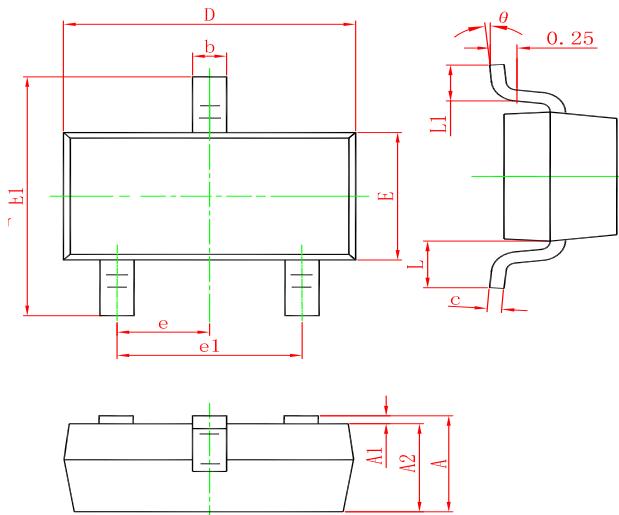


**Fig 15.** Typical Threshold Voltage Vs. Junction Temperature



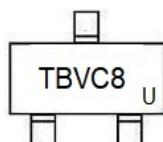
**Fig 16.** Typical Power Vs. Time

## SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## Marking



## Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRLML6246TR	SOT-23	3000	Tape and reel